IVSM12080HA2Z – 1200V 80mΩ Gen2 Automotive SiC MODULE

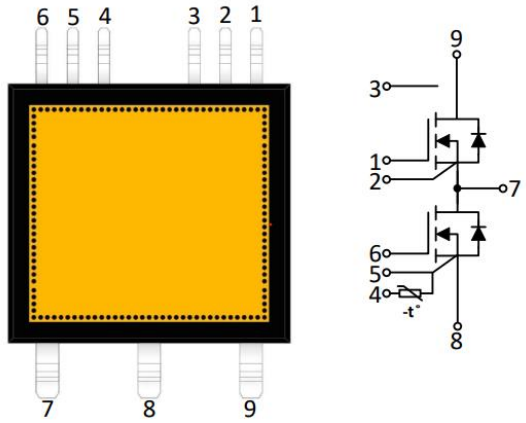
Features

- 2nd Generation SiC MOSFET Technology with +18V gate drive
- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- High operating junction temperature capability
- Very fast and robust intrinsic body diode
- Kelvin gate input easing driver circuit design
- Integrated NTC temperature sending

Applications

- Automotive OBC and DC/DC converters
- Automotive compressor inverters
- EV chargers
- Switch mode power supplies
- UPS and energy storage systems

Outline:



Marking Diagram:

IVSM12040HA2Z	Specific Device Code
XXXXX-XXXXX	Wafer Date Code
	IVCT logo
YYMMDDNNNNP	Lot No. include: YY(year) MM(month) DD(day) NNNN(serial No.) P(mass)
	2D Code (top side and bottom side): Device Code+ Lot No.

Absolute Maximum Ratings (Per leg/T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DS}	Drain-Source voltage	1200	V	V_{GS}=0V, I_D=100μA	
V_{GSmax} (DC)	Maximum DC voltage	-5 to 20	V	Static (DC)	
V_{GSmax} (Spike)	Maximum spike voltage	-10 to 23	V	Duty cycle<1%, and pulse width<200ns	
V_{GSon}	Recommended turn-on voltage	18±0.5	V		
V_{GSoff}	Recommended turn-off voltage	-3.5 to -2	V		
I_D	Drain current (continuous)	33	A	V_{GS}=18V, T_C=25°C	Fig. 23
		23	A	V_{GS}=18V, T_C=100°C	
I_{DM}	Drain current (pulsed)	82	A	Pulse width limited by SOA	Fig.25, 26
P_{TOT}	Total power dissipation	166	W	T_C=25°C	Fig. 24
T_{stg}	Storage temperature range	-55 to 175	°C		
T_J	Operating junction temperature	-55 to 175	°C		

Thermal Data

Symbol	Parameter	Value	Unit	Note
$R_{\theta(J-C)}$	Thermal Resistance from Junction to Case	0.903	°C/W	Fig. 25

Electrical Characteristics (Per leg/T_C=25°C unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
I_{DSS}	Zero gate voltage drain current		5	100	μA	V_{DS}=1200V, V_{GS}=0V	
I_{GSS}	Gate leakage current			±100	nA	V_{DS}=0V, V_{GS}=-5~20V	
V_{TH}	Gate threshold voltage	1.8	2.9	4.5	V	V_{GS}=V_{DS}, I_D=5mA	Fig. 8, 9
			2.1			V_{GS}=V_{DS}, I_D=5mA @ T_J=175°C	
R_{ON}	Static drain-source on-resistance		80	104	mΩ	V_{GS}=18V, I_D=10A @T_J=25°C	Fig. 4, 5, 6, 7
			150		mΩ	V_{GS}=18V, I_D=10A @T_J=175°C	
C_{iss}	Input capacitance		1160		pF	V_{DS}=800V, V_{GS}=0V, f=100kHz, V_{AC}=25mV	Fig. 16
C_{oss}	Output capacitance		82.4		pF		
C_{rss}	Reverse transfer capacitance		8.15		pF		
E_{oss}	C_{oss} stored energy		31		μJ		Fig. 17
Q_g	Total gate charge		53		nC	V_{DS}=800V, I_D=20A, V_{GS}=-3 to 18V	Fig. 18
Q_{gs}	Gate-source charge		14		nC		
Q_{gd}	Gate-drain charge		24		nC		
R_g	Gate input resistance		4.5		Ω	f=1MHz	
E_{ON}	Turn-on switching energy		277.3		μJ	V_{DS}=800V, I_D=20A, V_{GS}=-3.5 to 18V, $R_{G(ext)}$=3.3Ω, L=200μH T_J=25°C	Fig. 19, 20
E_{OFF}	Turn-off switching energy		46.0		μJ		
$t_{d(on)}$	Turn-on delay time		9.2		ns		
t_r	Rise time		14.4				
$t_{d(off)}$	Turn-off delay time		15.6				
t_f	Fall time		9.6				
E_{ON}	Turn-on switching energy		432.6		μJ	V_{DS}=800V, I_D=20A, V_{GS}=-3.5 to 18V, $R_{G(ext)}$=3.3Ω,L=200μH T_J=175°C	Fig. 22
E_{OFF}	Turn-off switching energy		42.9		μJ		

Reverse Diode Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V_{SD}	Diode forward voltage		4.0		V	I_{SD}=10A, V_{GS}=0V	Fig. 10, 11, 12
			3.8		V	I_{SD}=10A, V_{GS}=0V, T_J=175°C	
t_{rr}	Reverse recovery time		14.7		ns	V_{GS}=-3.5V/+18V, I_{SD}=20A, V_R=800V, $R_{G(ext)}$=13Ω L=200μH di/dt=3000A/μs	
Q_{rr}	Reverse recovery charge		358.8		nC		
I_{RRM}	Peak reverse recovery current		40		A		

NTC Thermistor Characteristics

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
R_{25}	Rated Resistance		10		kΩ	T_{NTC}=25℃	
ΔR/R	Deviation of R_{100}	-1		1	%		
$B_{25/85}$	B-Value		3610			$R_2=R_{25}\exp[B_{25/85}(1/T_2-1(298.15K))]$	
P_{25}	Power Dissipation			60	mW	Ta=25±0.5℃	

Typical Performance (curves)

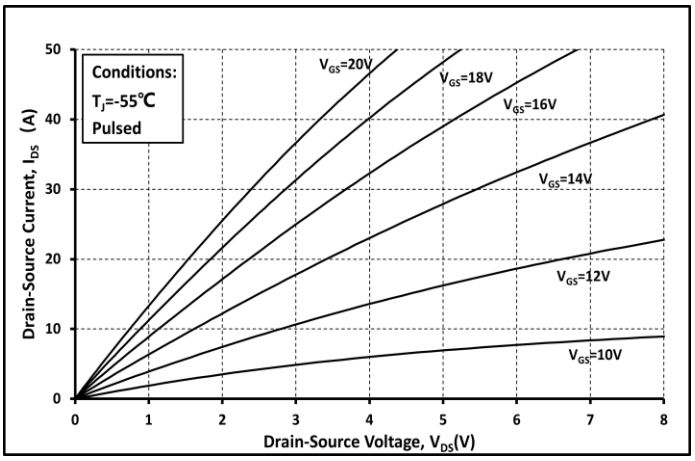


Fig. 1 Output Curve @ T_J=-55°C

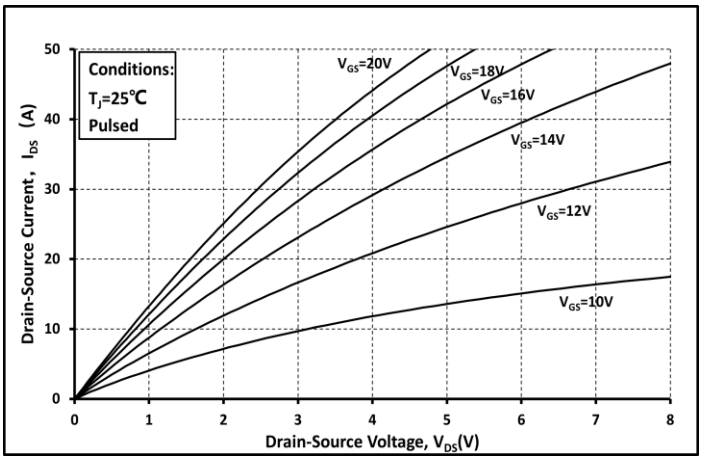


Fig. 2 Output Curve @ T_J=25°C

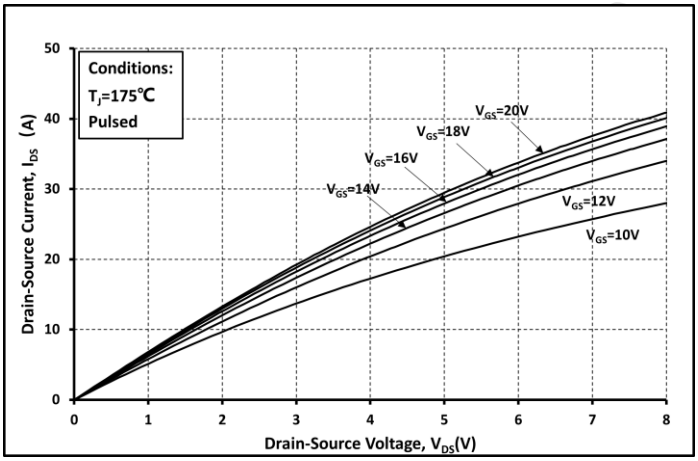


Fig. 3 Output Curve @ T_J=175°C

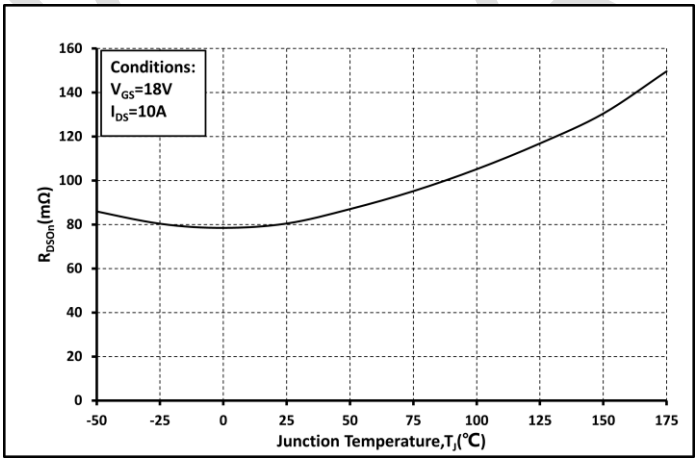


Fig. 4 Ron vs. Temperature

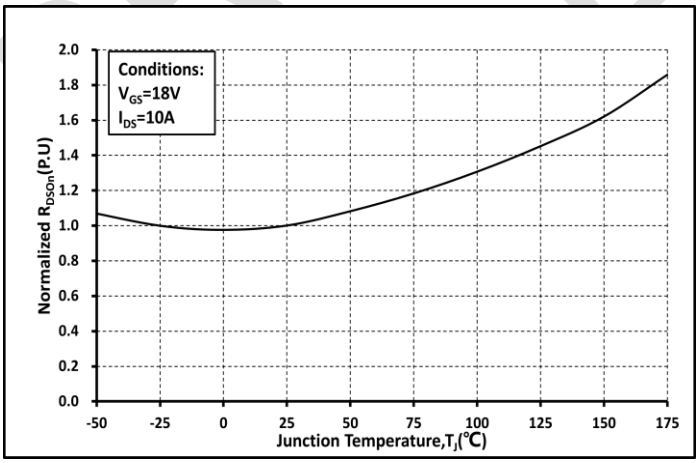


Fig. 5 Normalized Ron vs. Temperature

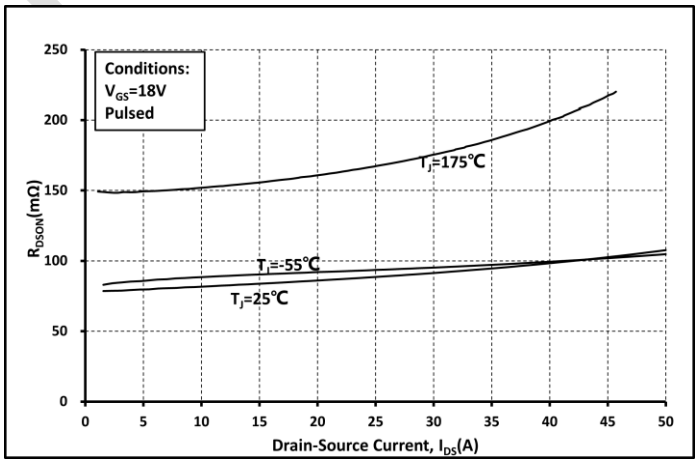


Fig. 6 Ron vs. I_{DS} @ Various Temperature

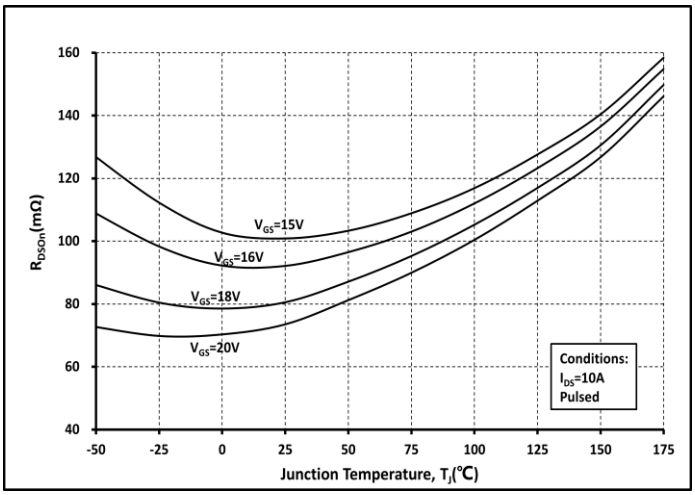


Fig. 7 Ron vs. Temperature @ Various V_{GS}

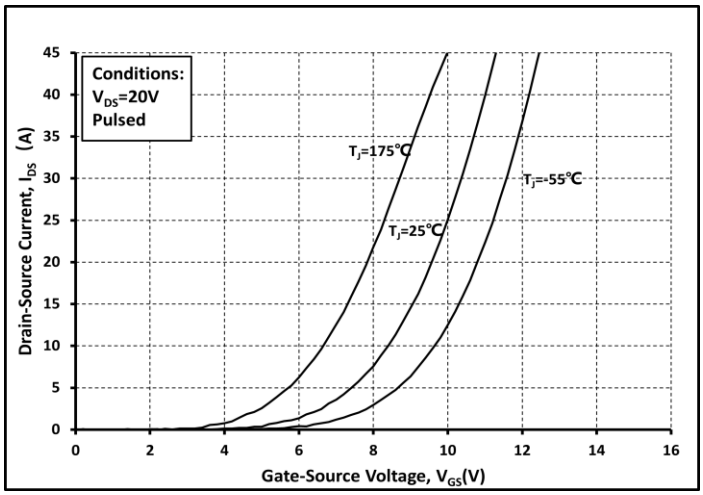


Fig. 8 Transfer Curves @ Various Temperature

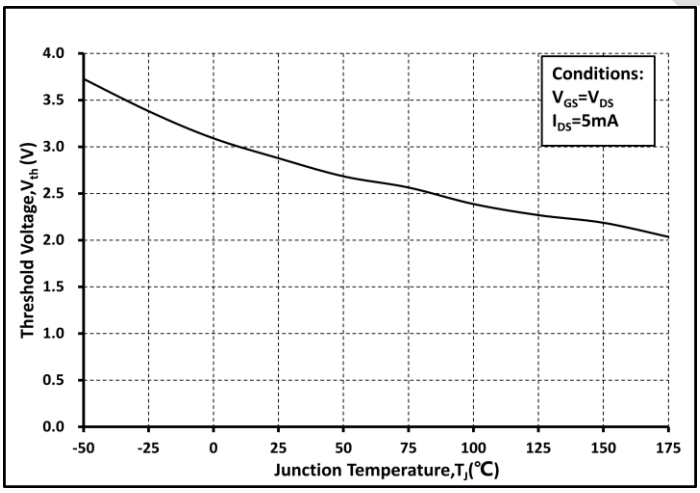


Fig. 9 Threshold Voltage vs. Temperature

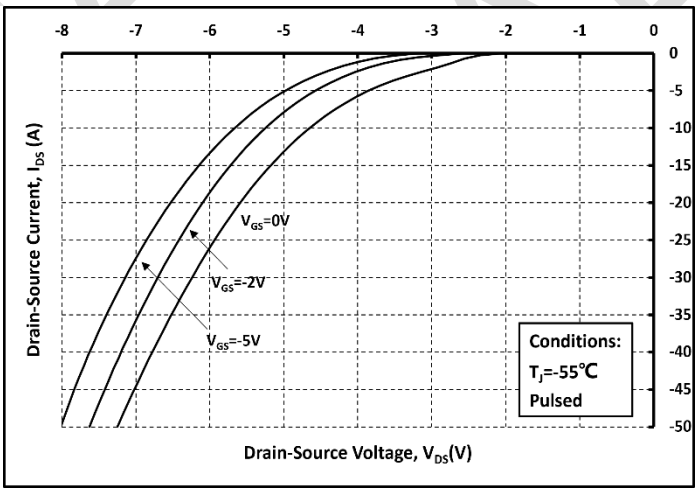


Fig. 10 Body Diode curves @ T_J=-55°C

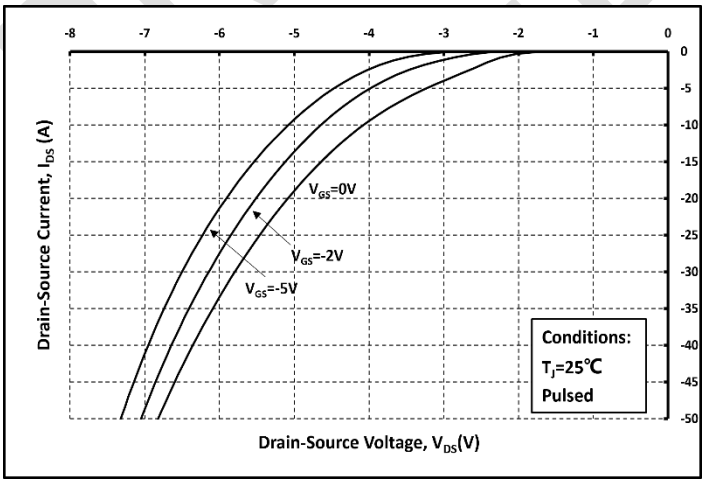


Fig. 11 Body Diode curves @ T_J=25°C

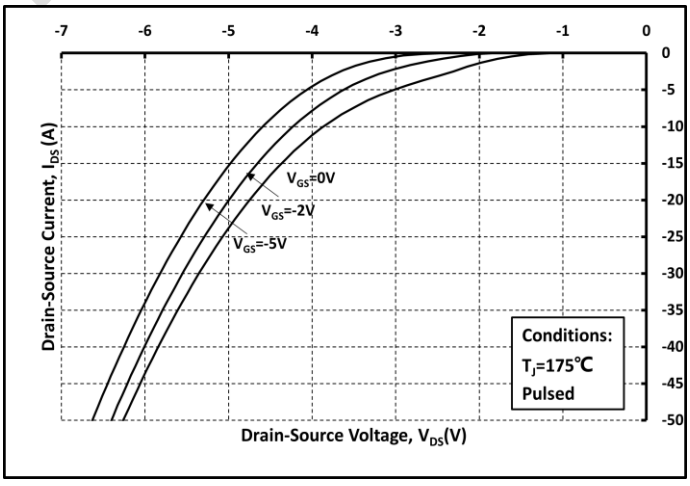


Fig. 12 Body Diode curves @ T_J=175°C

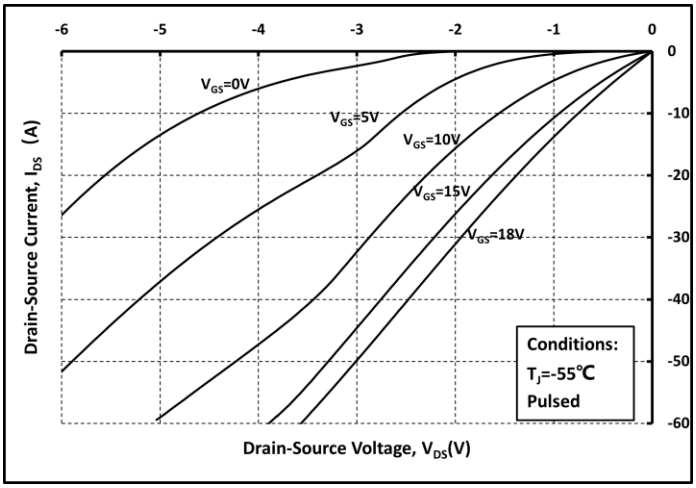


Fig. 13 3rd Quadrant curves @ T_J=-55°C

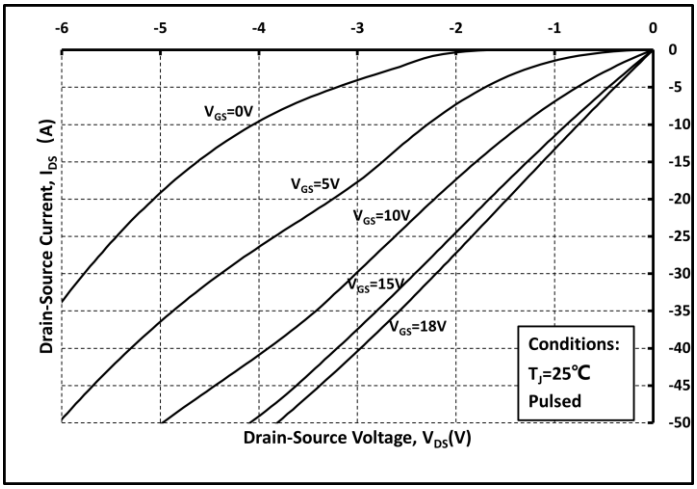


Fig. 14 3rd Quadrant curves @ T_J=25°C

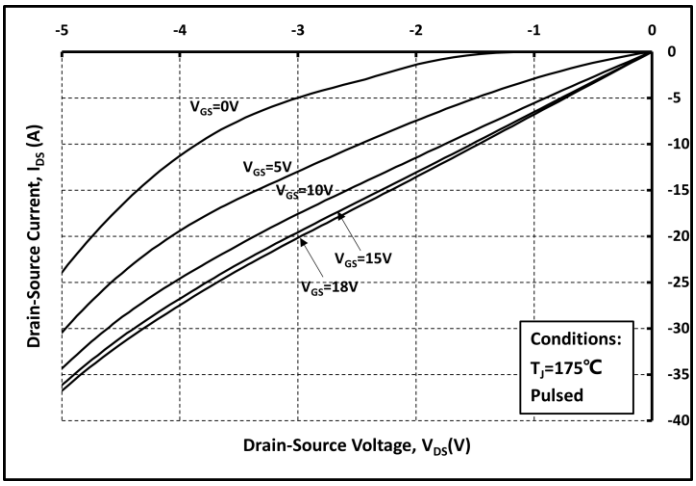


Fig. 15 3rd Quadrant curves @ T_J=175°C

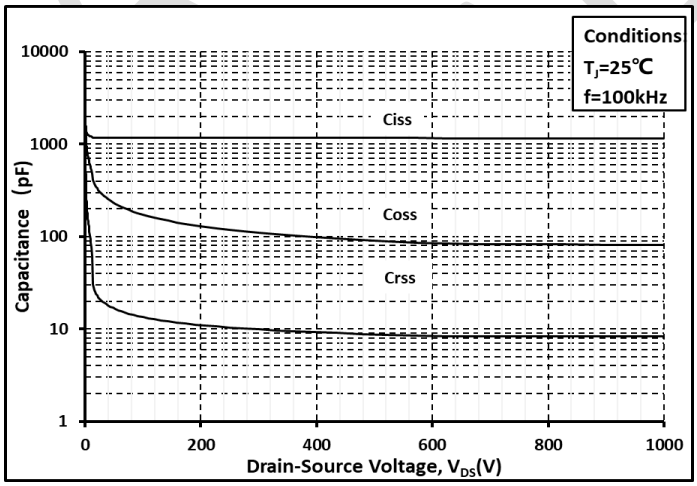


Fig. 16 Capacitance vs. V_{DS}

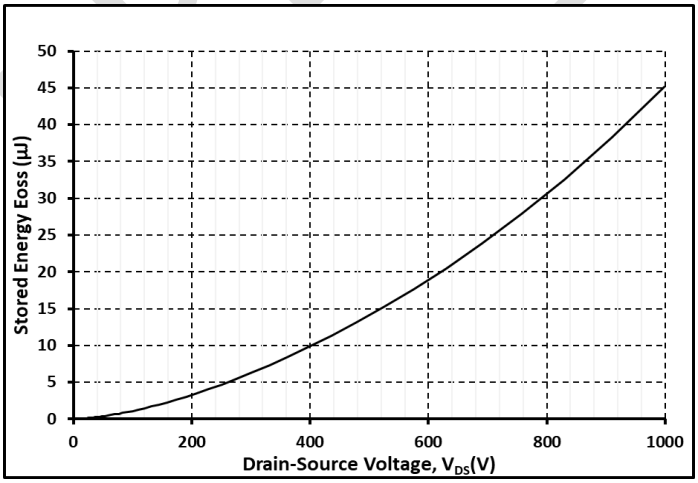


Fig. 17 Output Capacitor Stored Energy

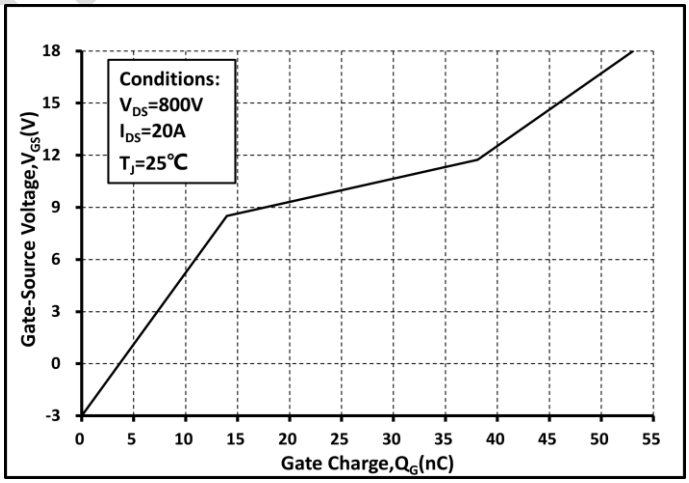


Fig. 18 Gate Charge Characteristics

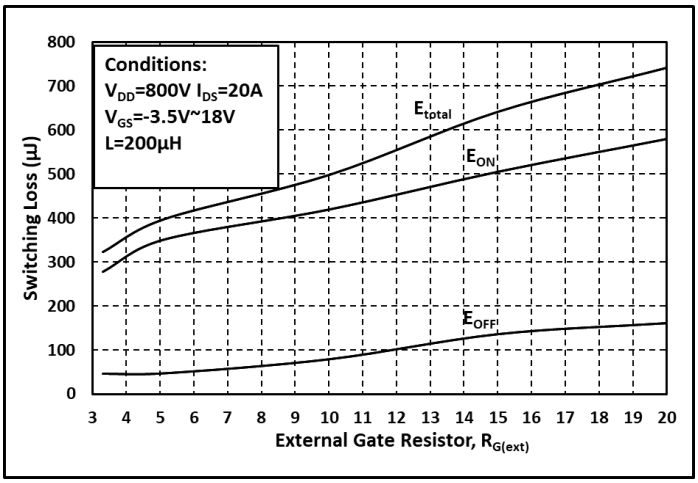


Fig. 19 Switching Energy vs. $R_{G(ext)}$

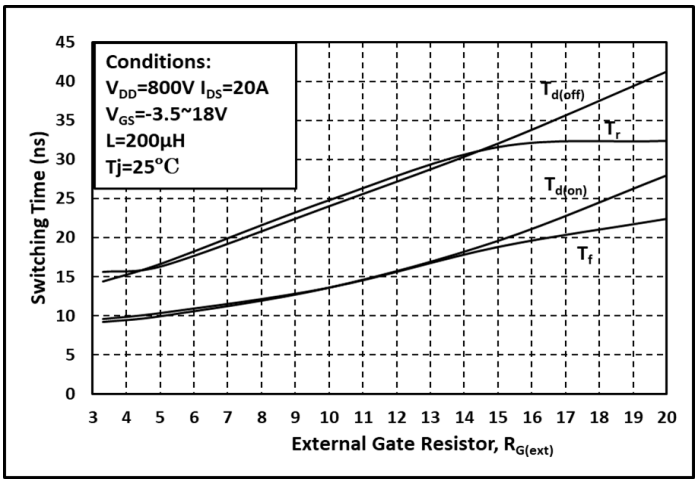


Fig. 20 Switching Times vs. $R_{G(ext)}$

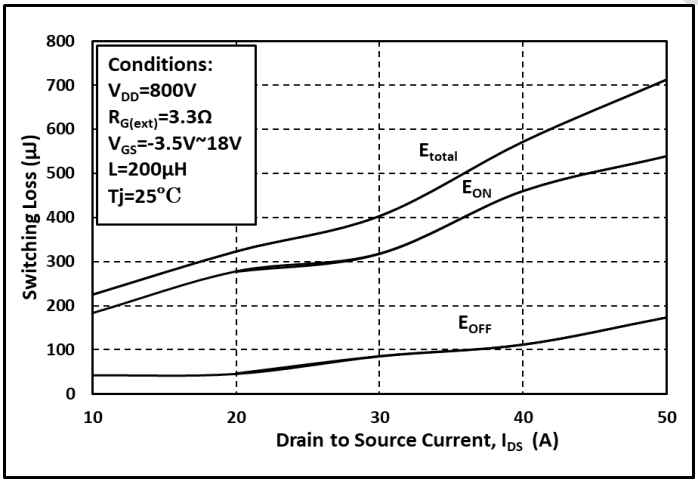


Fig. 21 Switching Energy vs. I_{DS}

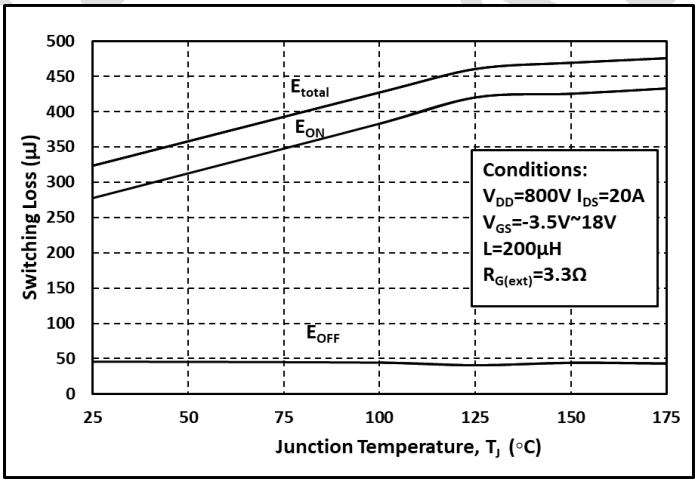


Fig. 22 Switching Energy vs. Temperature

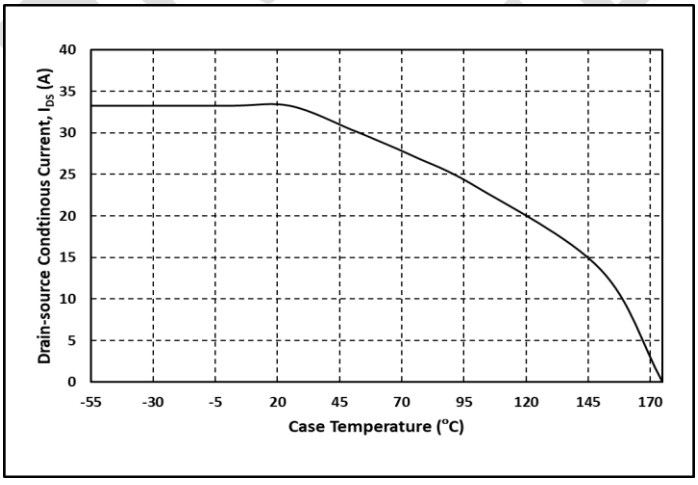


Fig. 23 Continuous Drain Current vs. Case Temperature

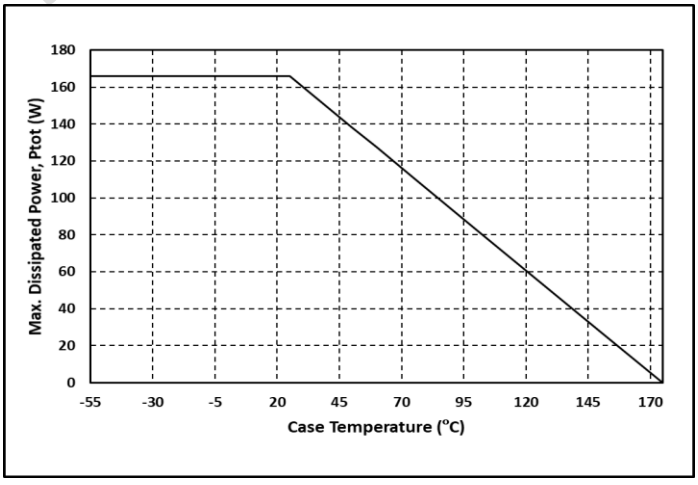


Fig. 24 Max. Power Dissipation Derating vs. Case Temperature

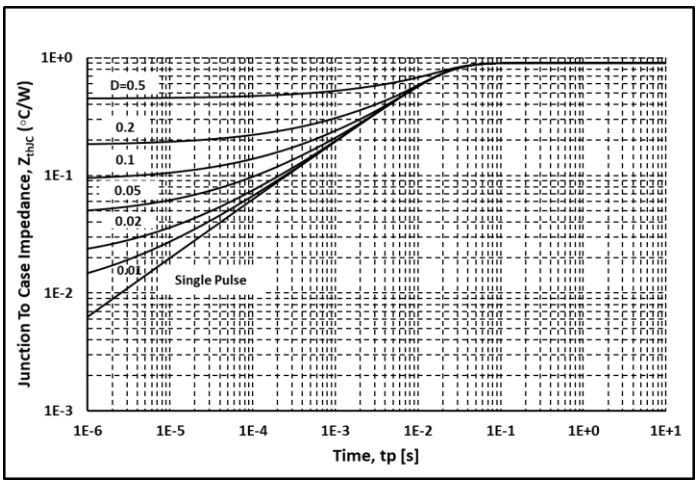


Fig. 25 Thermal impedance

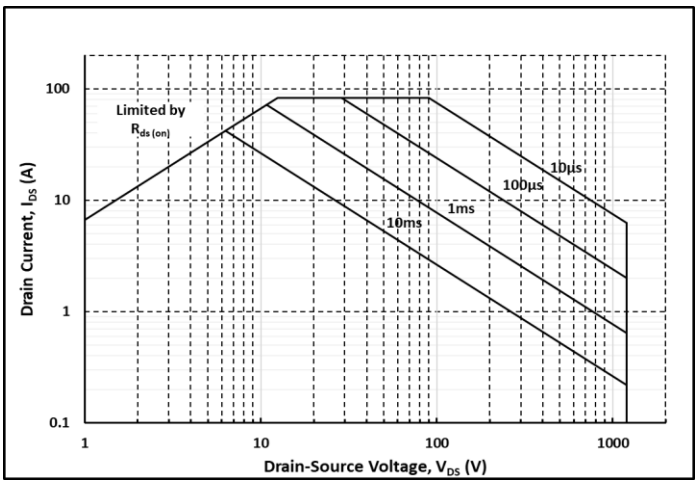
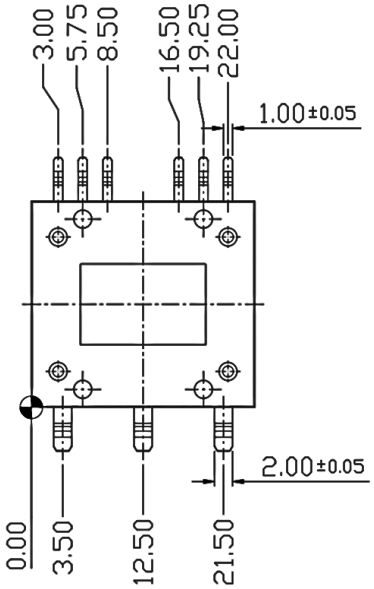
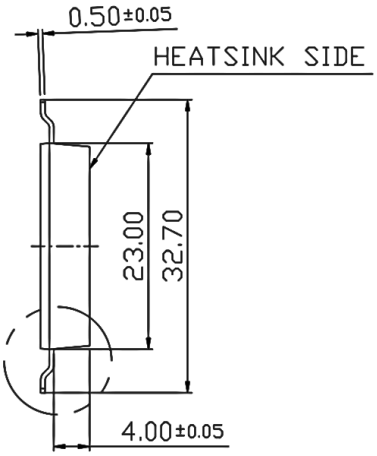
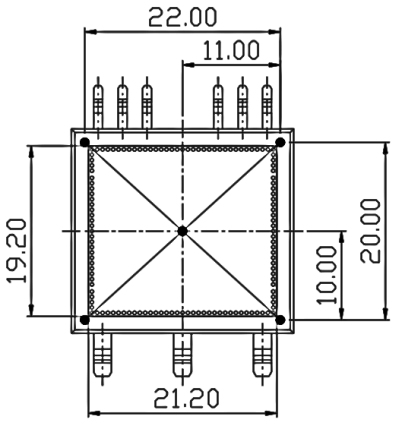


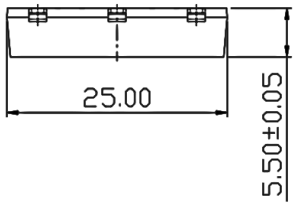
Fig. 26 Safe Operating Area

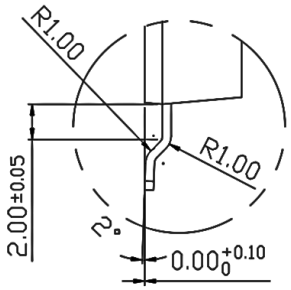
Package Dimensions (mm)







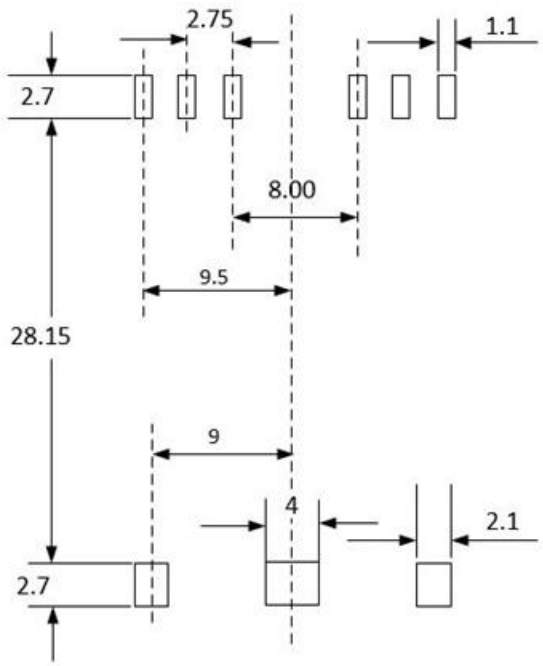




DETAIL A
SCALE 2:1

Note
1.General Tolerence ±0.2, ±0.5°
2.General C0.2×45° R0.5
3.Module Flatness Spec: 0-50um

Recommended footprint (mm)



NOTE:
8pin pad is enlarged to accommodate different packages.

Notes

For further information please contact IVCT's office.

The Information in this document is subject to change without notice.

Related Links

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